

NTE60 (NPN) & NTE61 (PNP) Silicon Complementary Transistors High Power Audio, Disk Head Positioner for Linear Applications

Description:

The NTE60 (NPN) and NTE61 (PNP) are complementary silicon power transistors in a TO3 type package designed for high power audio, disk head positioners, and other linear applications.

Features:

- High Safe Operating Area: 250W @ 50V
- For Low Distortion Complementary Designs
- High DC Current Gain: $h_{FE} = 25$ Min @ $I_C = 5A$

Absolute Maximum Ratings:

Collector–Emitter Voltage, $V_{CEO(sus)}$	140V
Collector–Base Voltage, V_{CBO}	140V
Emitter–Base Voltage, V_{EBO}	5V
Continuous Collector Current, I_C	20A
Continuous Base Current, I_B	5A
Continuous Emitter Current, I_E	25A
Total Power Dissipation ($T_C = +25^\circ C$), P_D	250W
Derate Above $25^\circ C$	1.43W/ $^\circ C$
Operating Junction Temperature Range, T_J	-65° to $+200^\circ C$
Storage Temperature Range, T_{stg}	-65° to $+200^\circ C$
Thermal Resistance, Junction–to–Case, R_{thJC}	0.70 $^\circ C/W$
Lead Temperature (During Soldering, 1/16" from Case, 10sec Max), T_L	$+265^\circ C$

Note 1. Matched complementary pairs are available upon request (NTE61MCP). Matched complementary pairs have their gain specification (h_{FE}) matched to within 10% of each other.

Electrical Characteristics: ($T_C = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics						
Collector–Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 200mA$, $I_B = 0$, Note 2	140	–	–	V
Collector Cutoff Current	I_{CEX}	$V_{CE} = 140V$, $V_{BE(off)} = 1.5V$	–	–	100	μA
		$V_{CE} = 140V$, $V_{BE(off)} = 1.5V$, $T_C = +150^\circ C$	–	–	2	mA
	I_{CEO}	$V_{CE} = 140V$, $I_B = 0$	–	–	250	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5V$, $I_C = 0$	–	–	100	μA

Note 2. Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2%.

Electrical Characteristics (Cont'd): ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Second Breakdown						
Second Breakdown Collector Current with Base Forward Bias	I _{S/b}	V _{CE} = 50V, t = 1s (non–repetitive)	5	–	–	μA
		V _{CE} = 100V, t = 1s (non–repetitive)	1	–	–	μA
ON Characteristics						
DC Current Gain	h _{FE}	V _{CE} = 2V, I _C = 5A	25	–	150	
Collector–Emitter Saturation Voltage	V _{CE(sat)}	I _C = 5A, I _B = 500mA	–	–	1	V
Base–Emitter On Voltage	V _{BE(on)}	V _{CE} = 2V, I _C = 5A	–	–	2	V
Dynamic Characteristics						
Current Gain–Bandwidth Product	f _T	V _{CE} = 10V, I _C = 500mA, f _{test} = 0.5MHz	2	–	–	MHz
Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f _{test} = 1MHz	–	–	1000	pF

